



## IN4148

SILICON EPITAXIAL PLANAR  
SWITCHING DIODE

TECHNICAL  
SPECIFICATION

**REVERSE VOLTAGE: 75V**  
**FORWARD CURRENT: 150mA**

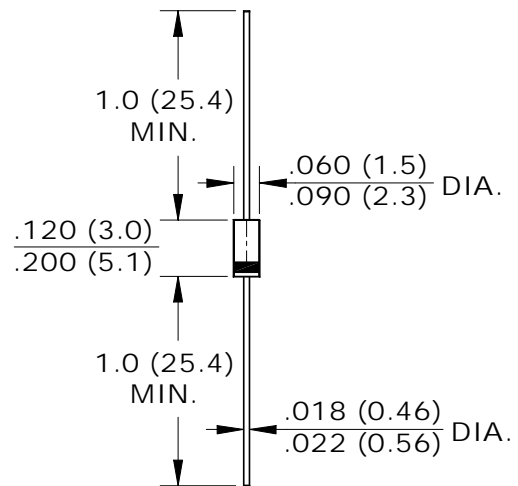
### FEATURES

- Small glass structure ensures high reliability
- Fast switching
- Low leakage
- High temperature soldering guaranteed:  
250°C/10S/9.5mm lead length  
at 5 lbs tension

### MECHANICAL DATA

- Terminal: Plated axial leads solderable per  
MIL-STD 202E, method 208C
- Case: Glass, hermetically sealed
- Polarity: Color band denotes cathode
- Mounting position: Any

### DO - 35



Dimensions in inches and (millimeters)

### MAXIMUM RATINGS AND CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

RATINGS	SYMBOL	VALUE	UNITS
Reverse Voltage	$V_R$	75	V
Peak Reverse Voltage	$V_{RM}$	100	V
Forward Current (average)	$I_O$	150	mA
Repetitive Forward Peak Current	$I_{FRM}$	300	mA
Forward Voltage ( $I_F=10mA$ )	$V_F$	1	V
Reverse Current ( $V_R=20V$ )	$I_{R1}$	25	nA
Reverse Current ( $V_R=75V$ )		5	$\mu A$
Reverse Current ( $V_R=20V, T_J=100^\circ C$ )	$I_{R2}$	50	$\mu A$
Capacitance (note 1)	$C_t$	4	pF
Reverse Recovery Time (note 2)	$I_F$	4	nS
Thermal Resistance (junction to ambient) (note 3)	$R_{\theta(ja)}$	0.35	$^\circ C/mW$
Operating Junction and Storage Temperature Range	$T_{STG}, T_J$	-55 ~ +175	$^\circ C$

Notes:

- 1:  $V_R=0V, f=1\text{ MHz}$
- 2:  $I_F=10mA$  to  $I_R=1mA, V_R=6V, R_L=100\Omega$
- 3: Valid provided that leads are kept at ambient temperature at a distance of 8mm from case.